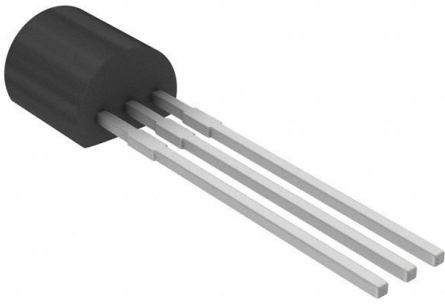


# PBSS5140S,126 Datasheet

[www.digi-electronics.com](http://www.digi-electronics.com)



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	PBSS5140S,126-DG
Manufacturer	<a href="#">NXP USA Inc.</a>
Manufacturer Product Number	PBSS5140S,126
Description	TRANS PNP 40V 1A TO92-3
Detailed Description	Bipolar (BJT) Transistor PNP 40 V 1 A 150MHz 830 mW Through Hole TO-92-3



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

PBSS5140S,126

Series:

-

Transistor Type:

PNP

Voltage - Collector Emitter Breakdown (Max):

40 V

Current - Collector Cutoff (Max):

100nA

Power - Max:

830 mW

Operating Temperature:

150°C (TJ)

Package / Case:

TO-226-3, TO-92-3 (TO-226AA) Formed Leads

Base Product Number:

PBSS5

Manufacturer:

NXP USA Inc.

Product Status:

Obsolete

Current - Collector (Ic) (Max):

1 A

Vce Saturation (Max) @ Ib, Ic:

500mV @ 100mA, 1A

DC Current Gain (hFE) (Min) @ Ic, Vce:

300 @ 100mA, 5V

Frequency - Transition:

150MHz

Mounting Type:

Through Hole

Supplier Device Package:

TO-92-3

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0075

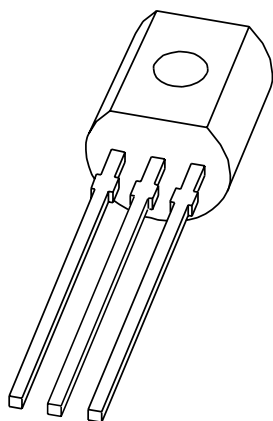
Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

# DATA SHEET



**PBSS5140S**

**40 V low  $V_{CEsat}$  PNP transistor**

Product data sheet  
Supersedes data of 2001 Nov 15

2004 Aug 13

**40 V low  $V_{CEsat}$  PNP transistor****PBSS5140S****FEATURES**

- High power dissipation (830 mW)
- Ultra low collector-emitter saturation voltage
- 1 A continuous current
- High current switching
- Improved device reliability due to reduced heat generation.

**APPLICATIONS**

- Medium power switching and muting
- Linear regulators
- DC/DC converter
- LCD back-lighting
- Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

**DESCRIPTION**

PNP low  $V_{CEsat}$  transistor in a SOT54 plastic package.  
NPN complement: PBSS4140S.

**MARKING**

TYPE NUMBER	MARKING CODE
PBSS5140S	S5140S

**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	-40	V
$I_C$	collector current (DC)	-1	A
$I_{CM}$	peak collector current	-2	A
$R_{CEsat}$	equivalent on-resistance	<500	m $\Omega$

**PINNING**

PIN	DESCRIPTION
1	base
2	collector
3	emitter

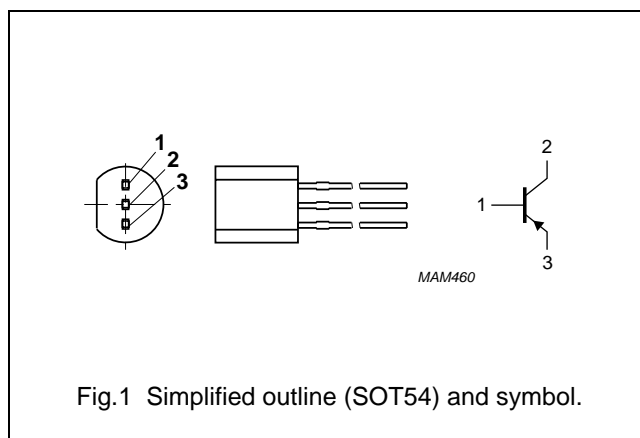


Fig.1 Simplified outline (SOT54) and symbol.

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	-	-40	V
$V_{CEO}$	collector-emitter voltage	open base	-	-40	V
$V_{EBO}$	emitter-base voltage	open collector	-	-5	V
$I_C$	collector current (DC)		-	-1	A
$I_{CM}$	peak collector current		-	-2	A
$I_{BM}$	peak base current		-	-1	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$ ; note 1	-	830	mW
$T_{stg}$	storage temperature		-65	+150	$^\circ\text{C}$
$T_j$	junction temperature		-	150	$^\circ\text{C}$
$T_{amb}$	operating ambient temperature		-65	+150	$^\circ\text{C}$

**Note**

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.

40 V low  $V_{CEsat}$  PNP transistor

PBSS5140S

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	150	K/W

## Note

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

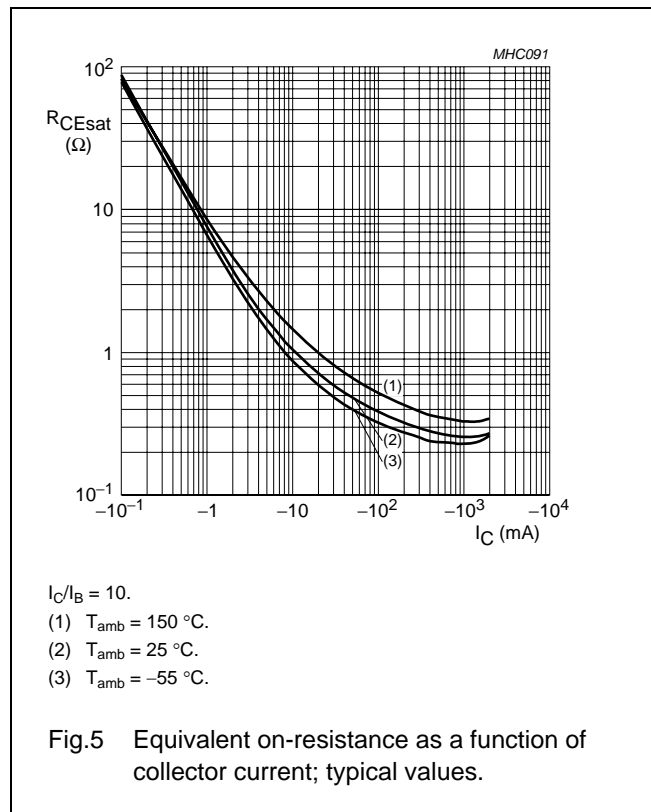
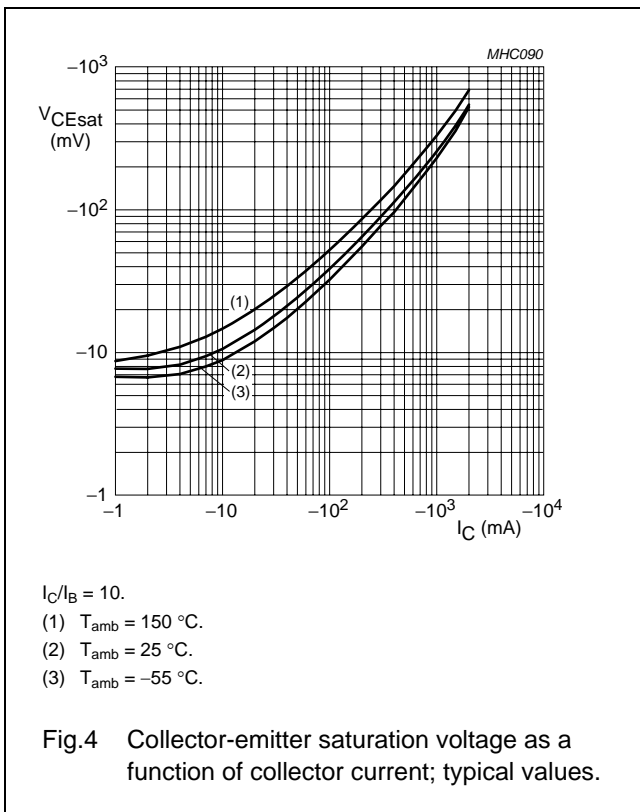
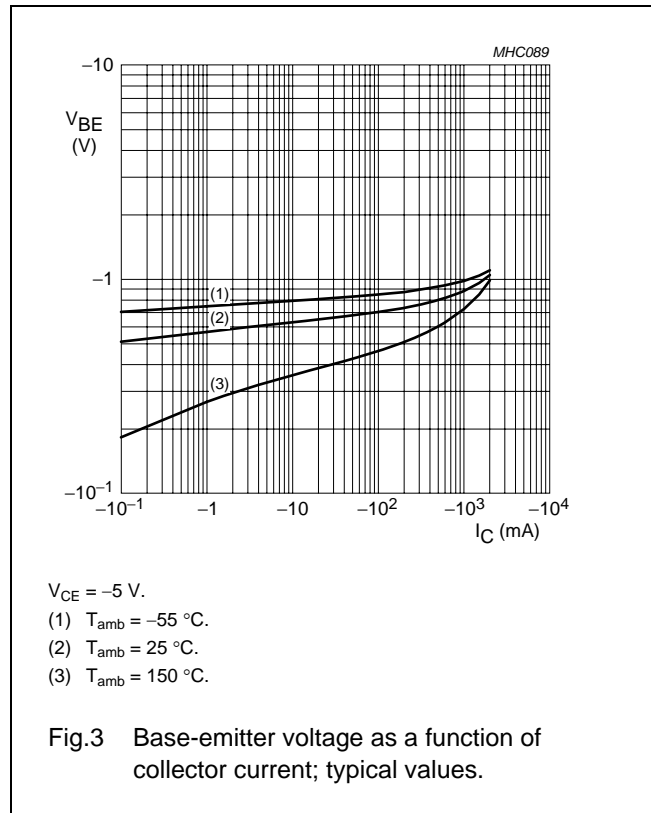
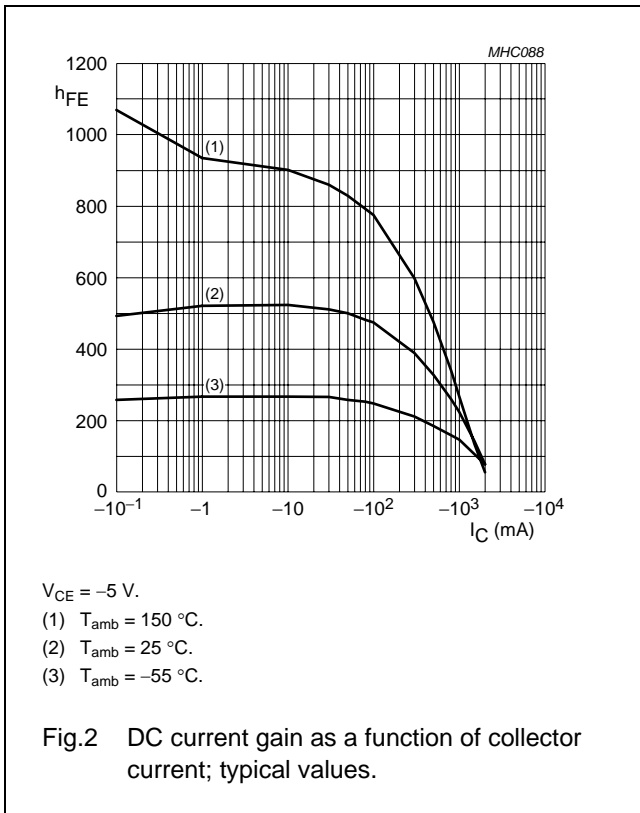
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -40\text{ V}; I_C = 0$	–	–	–100	nA
		$V_{CB} = -40\text{ V}; I_C = 0; T_J = 150\text{ °C}$	–	–	–50	$\mu\text{A}$
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = -30\text{ V}; I_B = 0$	–	–	–100	nA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0$	–	–	–100	nA
$h_{FE}$	DC current gain	$V_{CE} = -5\text{ V}; I_C = -1\text{ mA}$	300	–	–	
		$V_{CE} = -5\text{ V}; I_C = -100\text{ mA}$	300	–	800	
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$	250	–	–	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	160	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	–	–	–200	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–	–250	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$	–	–	–500	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA}; \text{note 1}$	–	300	<500	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–	–1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	–	–	–1	V
$f_T$	transition frequency	$I_C = -50\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$	150	–	–	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	–	12	pF

## Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

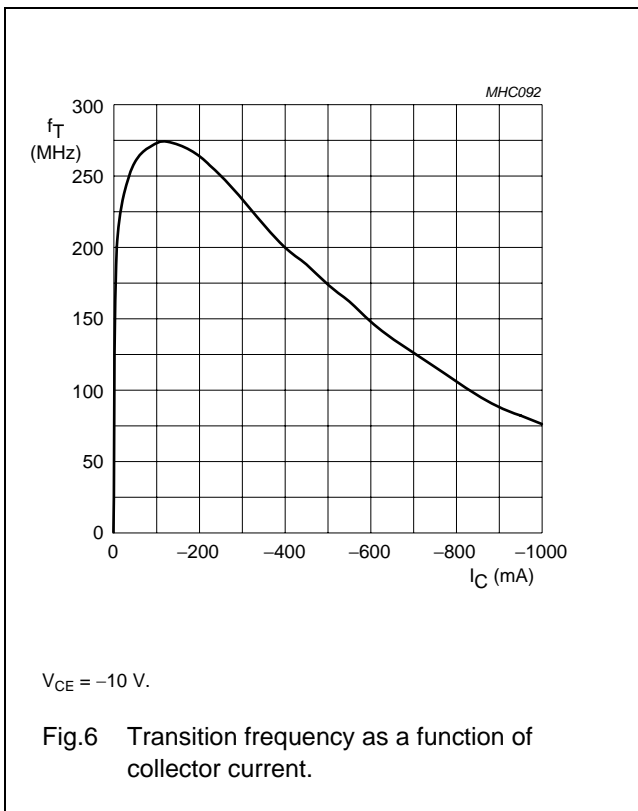
40 V low  $V_{CEsat}$  PNP transistor

PBSS5140S



40 V low  $V_{CEsat}$  PNP transistor

PBSS5140S



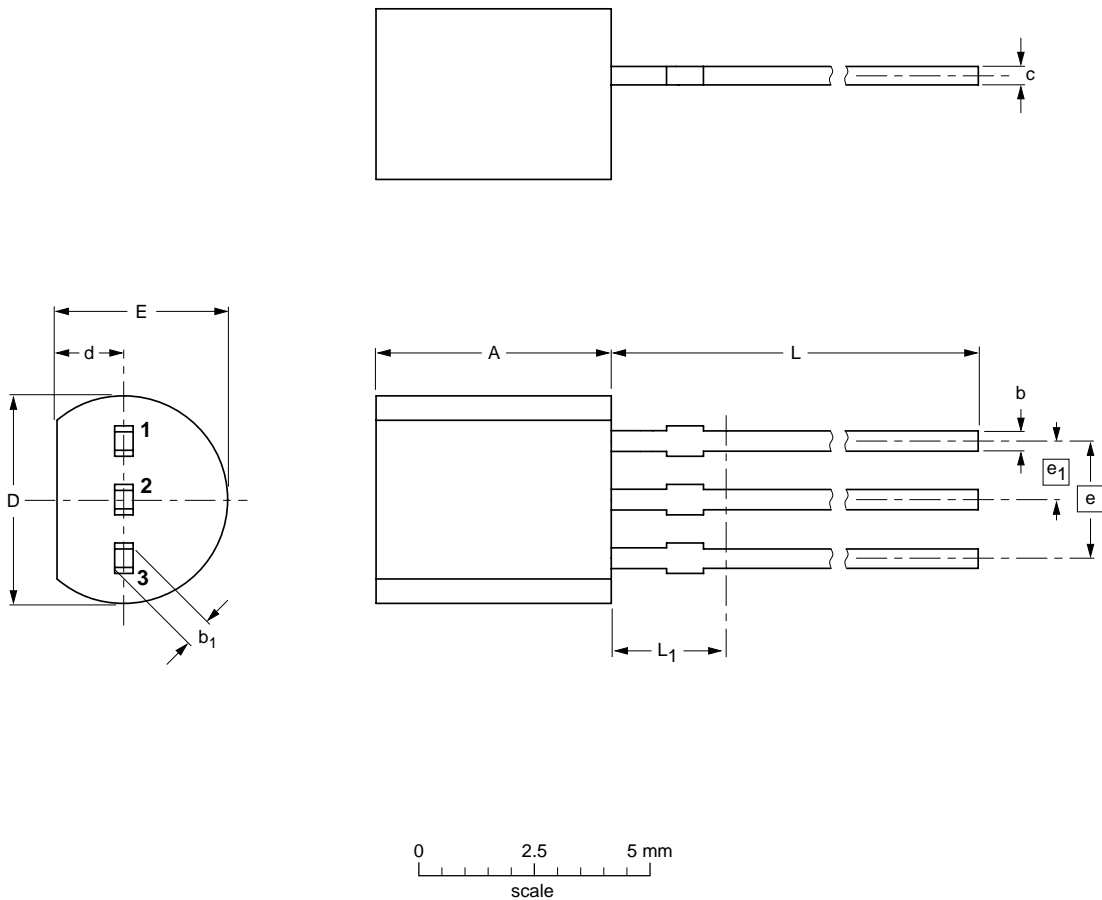
40 V low  $V_{CEsat}$  PNP transistor

PBSS5140S

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	b	b <sub>1</sub>	c	D	d	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

**Note**

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT54		TO-92	SC-43A		04-06-28 04-11-16



40 V low  $V_{CEsat}$  PNP transistor

PBSS5140S

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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